

MH283 is an unipolar Hall effect sensor IC. It incorporates advanced chopper stabilization technology to provide accurate and stable magnetic switch points. The design, specifications and performance have been optimized for applications of solid state switches.

The output transistor will be switched on (BOP) in the presence of a sufficiently strong South pole magnetic field facing the marked side of the package. Similarly, the output will be switched off (BRP) in the presence of a weaker South field and remain off with "0" field. The Pull high resistor has been integrated.

The package type is in a Green version was verified by third party Lab.

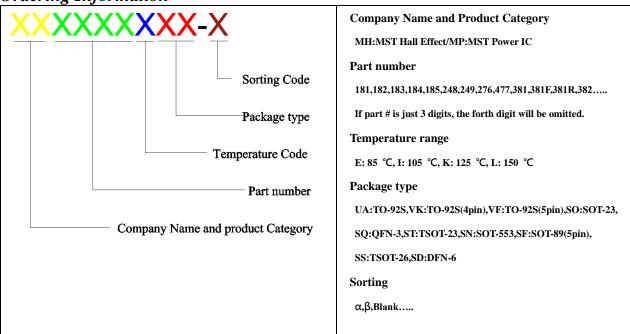
### Features and Benefits

- DMOS Hall IC Technology.
- Reverse bias protection on power supply pin.
- Solid-State Reliability.
- Chopper stabilized amplifier stage.
- Unipolar, output switches with absolute value of South pole from magnet.
- Operation down to 3.0V.
- High Sensitivity for direct reed switch replacement applications.
- 100% tested at 125°Cfor K Spec.
- Custom sensitivity / Temperature selection are available.
- Good ESD Protection.
- RoHS compliant 2011/65/EU and Halogen Free

#### **Applications**

- Solid state switch
- Limit switch
- Current limit
- Interrupter
- Current sensing
- Magnet proximity sensor for reed switch replacement

# Ordering Information

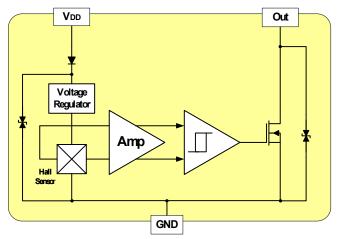




Part No.	Temperature Suffix	Package Type	
MH283KUA	K $(-40^{\circ}C \text{ to} + 125^{\circ}C)$	UA (TO-92S)	
MH283KSO	K (-40°C to $+ 125$ °C)	SO (SOT-23)	
MH283EUA	E (-40°C to $+ 85$ °C)	UA (TO-92S)	
MH283ESO	$E (-40^{\circ}C \text{ to } + 85^{\circ}C)$	SO (SOT-23)	

KUA spec is using in industrial and automotive application. Special Hot Testing is utilized.

## Functional Diagram



*Note:* Static sensitive device; please observe ESD precautions. Reverse  $V_{DD}$  protection is not included. For reverse voltage protection, a  $11K\Omega$  resistor in series with  $V_{DD}$  is recommended.

## Absolute Maximum Ratings At (Ta=25°C)

Characteristics			Values		Unit	
Supply voltage, (V <sub>DD</sub> )				28	V	
Output Voltage, (V <sub>OUT</sub> )				28		
Reverse Voltage, (V <sub>DD</sub> )				-27	V	
Magnetic flux density			Uı	nlimited	Gauss	
Output current, ( <i>I</i> <sub>OUT</sub> )			50 m			
Operating Temperature Ra	ange,	"E" version	-4(	) to +85	°C	
( <i>Ta</i> )		"K" version	-40	to +125	°C	
Storage temperature range, ( <i>Ts</i> )			-55	to +150	°C	
Maximum Junction Temp,( <i>Tj</i> )			150	°C		
Thermal Resistance	$(\theta ja)$ UA / SO		20	6 / 543	°C/W	
Thermai Resistance	$(\theta jc)$ UA / SO		14	8 / 410	°C/W	
Package Power Dissipation, $(P_D)$ UA / SO		606 / 230		mW		

*Note:* Do not apply reverse voltage to V<sub>DD</sub> and V<sub>OUT</sub> Pin, It may be caused for Miss function or damaged device.

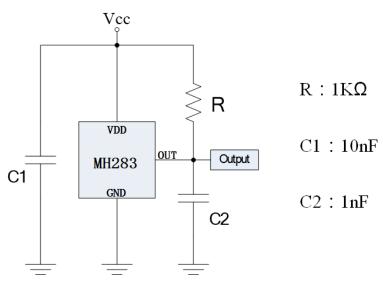


# **Electrical Specifications**

DC Operating Parameters TA=+25°C, VDD=12V (Unless otherwise specified)

Parameters	Test Conditions	Min	Тур	Max	Units
Supply Voltage,(VDD)	Operating	3.0		24.0	V
Supply Current,( <i>IDD</i> )	B <bop< td=""><td></td><td>2.5</td><td>5.0</td><td>mA</td></bop<>		2.5	5.0	mA
Output Saturation Voltage, ( <i>Vsat</i> )	Iout = 20 mA, B>BOP			500.0	mV
Output Leakage Current, ( <i>loff</i> )	IOFF B <brp, vout="20V&lt;/td"><td></td><td></td><td>10.0</td><td>uA</td></brp,>			10.0	uA
Output Rise Time, ( <i>TR</i> )	RL=1k $\Omega$ , CL =20pF		0.04	0.45	uS
Output Fall Time, (TF)	RL=820Ω; CL =20pF		0.18	0.45	uS
Electro-Static Discharge	HBM	4			KV
Operate Point (B <sub>OP</sub> )		90		150	Gauss
Release Point (B <sub>RP</sub> )		40		100	Gauss
Hysteresis (B <sub>HYS</sub> )			50		Gauss

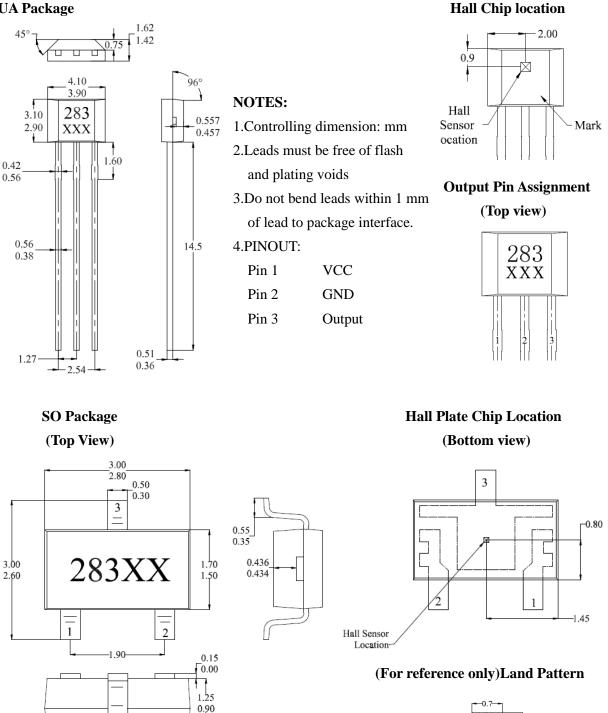
# Typical application circuit





## Sensor Location, Package Dimension and Marking

#### **UA Package**



#### **NOTES:**

- 1.PINOUT (See Top View at left :)
  - Pin 1  $V_{CC}$
  - Pin 2 Output
  - Pin 3 GND
- 2.Controlling dimension: mm

3.Lead thickness after solder plating will be 0.254mm maximum

